/ Descriptions

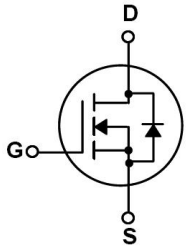
/ Features

≤ Ω Ω

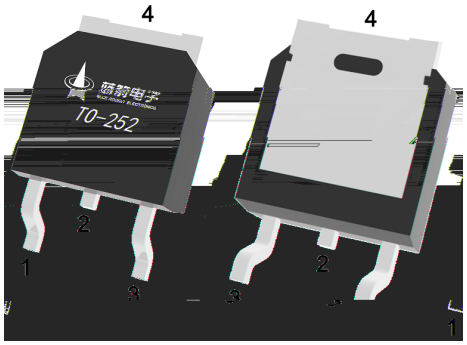
≤ Ω Ω

/ Applications

/ Equivalent Circuit



/ Pinning



/ Marking

						μ
						Ω

/ Electrical Characteristics(Tc=25)

		μ				
–						
–						μ
						Ω

/ Electrical Characteristic Curve

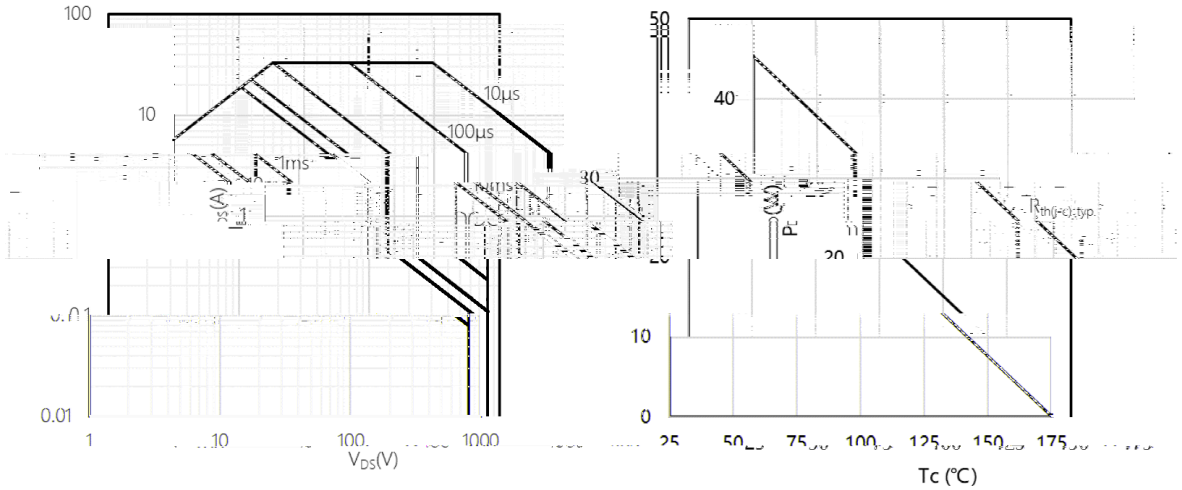


Fig1. Safe operating area (SOA)

Fig2. Power dissipation

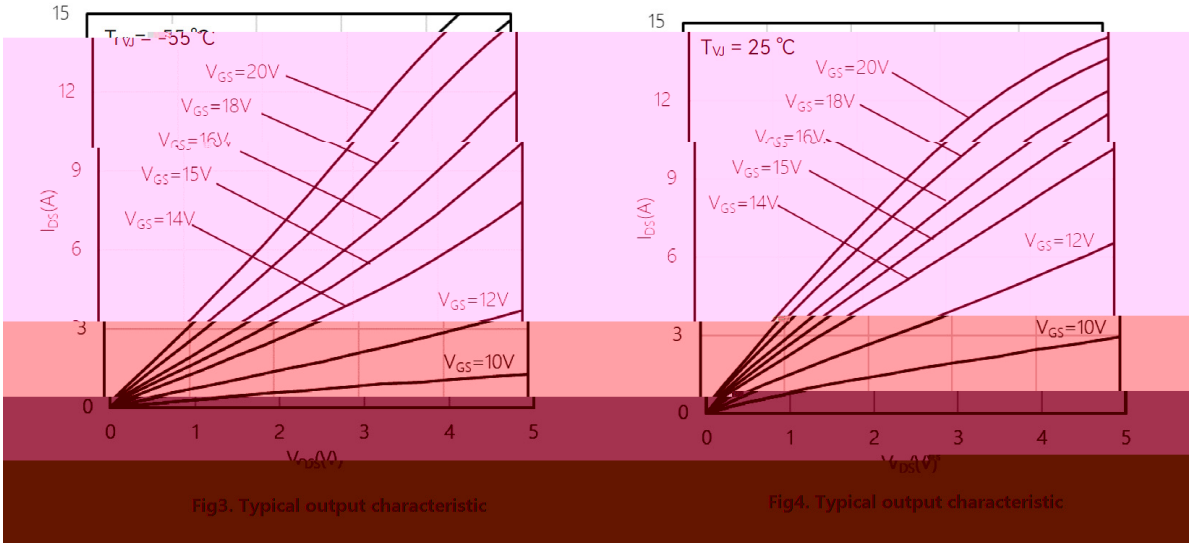


Fig3. Typical output characteristic

Fig4. Typical output characteristic

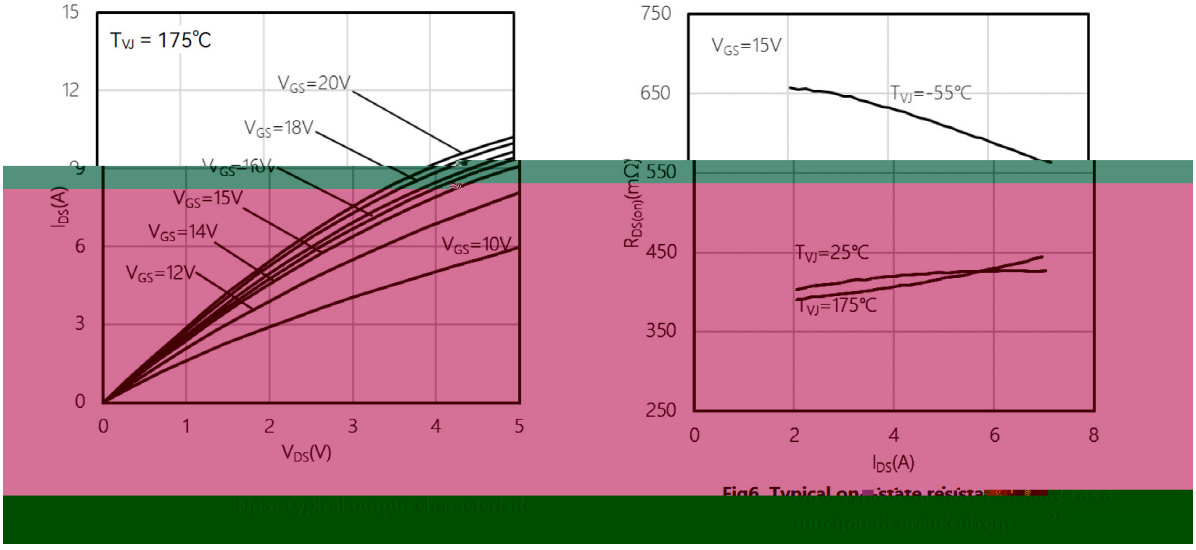


Fig5. Typical output characteristic

Fig6. Typical on-state resistance as a function of drain current

/ Electrical Characteristic Curve

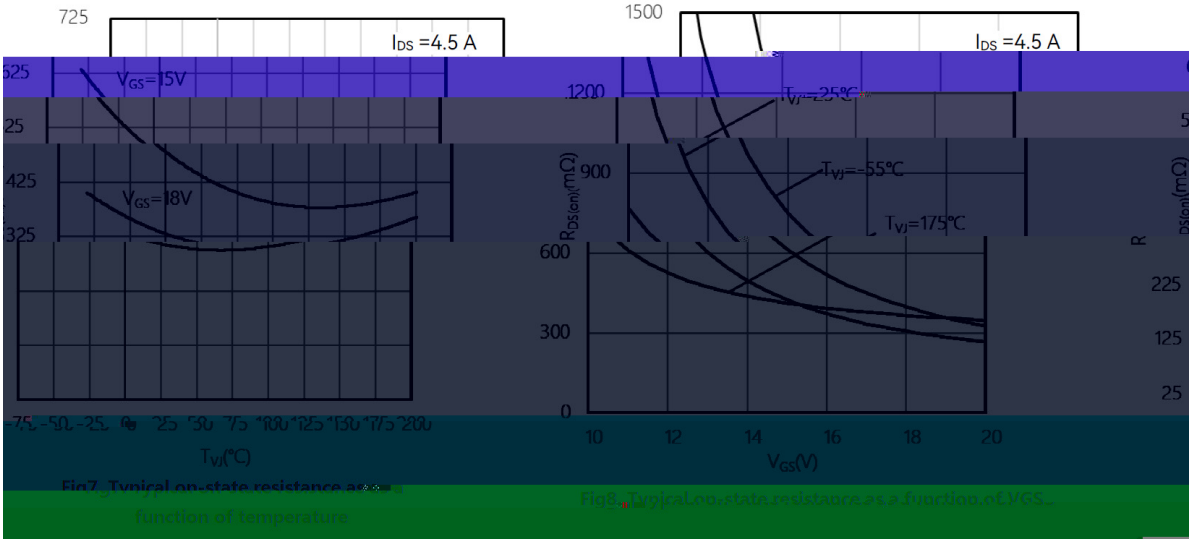
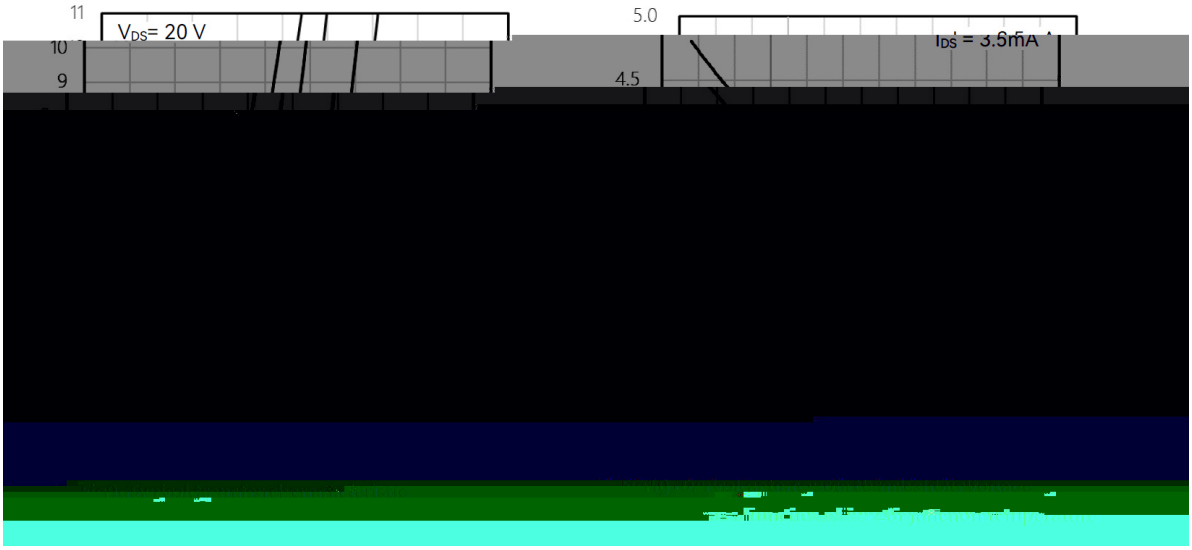


Fig7. Typical on-state resistance as a function of temperature

Fig8. Typical on-state resistance as a function of V_{GS}



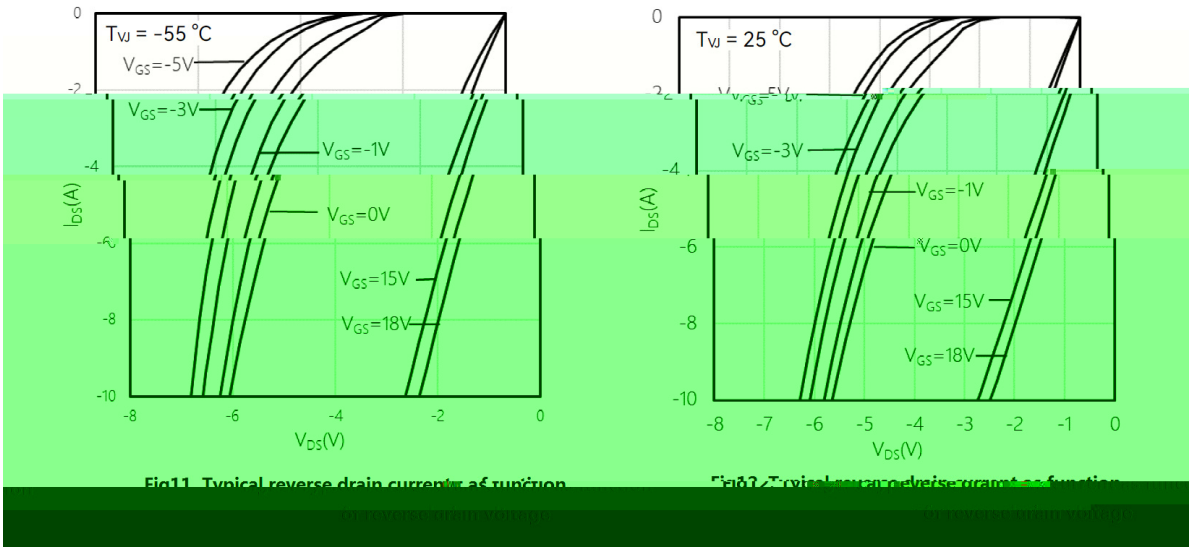


Fig11. Typical reverse drain current as function of reverse drain voltage

Fig12. Typical reverse drain current as function of reverse drain voltage

/ Electrical Characteristic Curve

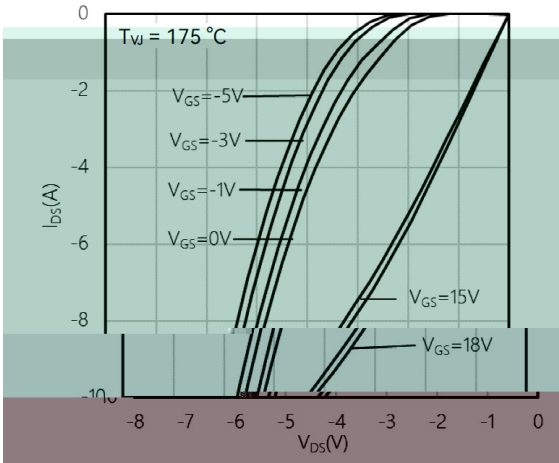


Fig13. Typical reverse drain current as function of reverse drain voltage

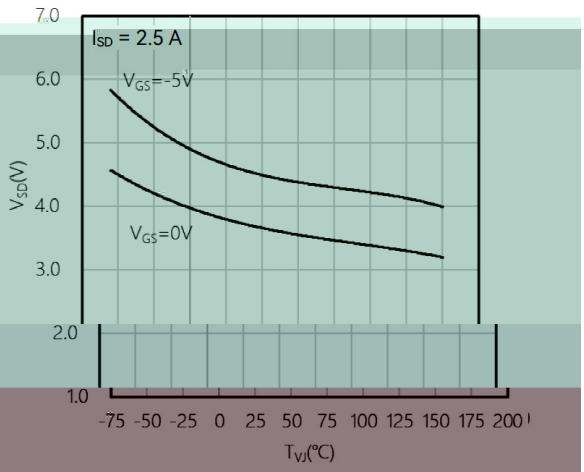


Fig14. Typical reverse drain voltage as function of junction temperature

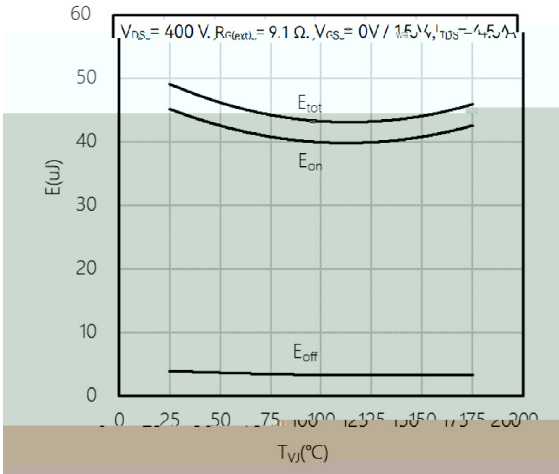


Fig15. Typical switching energy as a function of junction temperature, 2nd device own body diode: VGS = 0 V

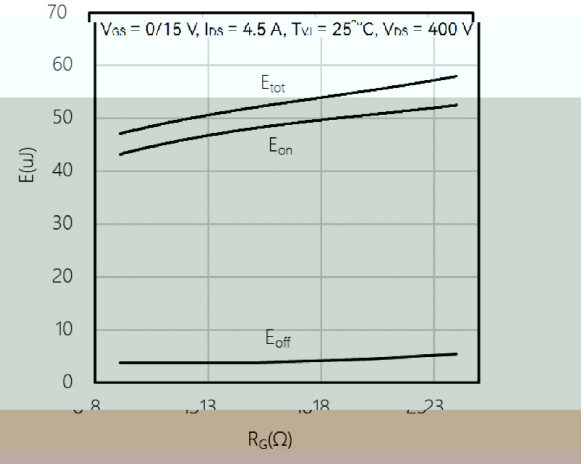


Fig16. Typical switching energy losses as a function of gate resistance, 2nd device own body diode: VGS = 0 V

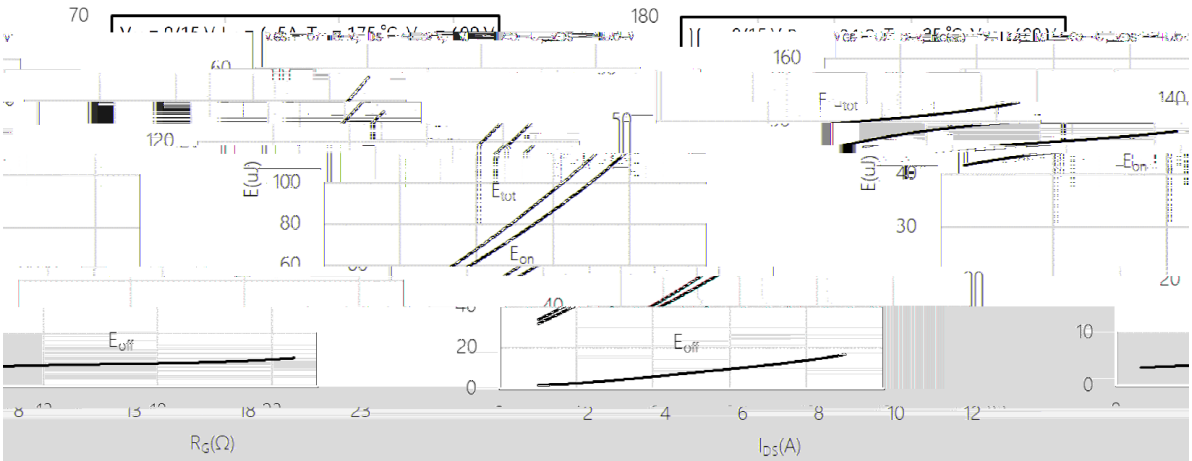


Fig17. Typical switching energy losses as a function of gate resistance, 2nd device own body diode: VGS = 0V

Fig18. Typical switching energy losses as a function of IDS, 2nd device own body diode: VGS = 0V

/ Electrical Characteristic Curve

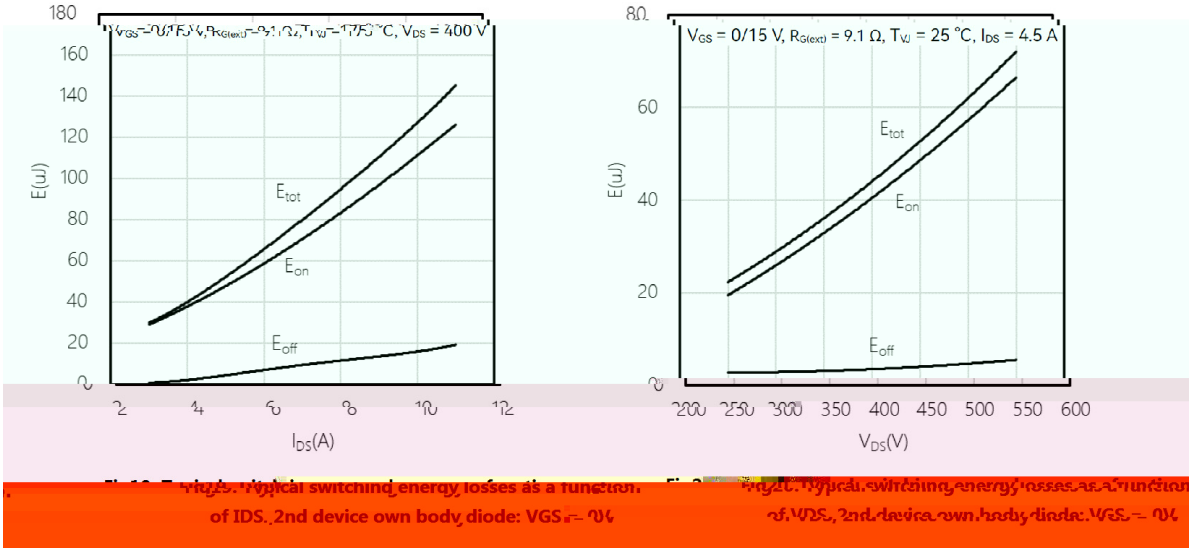


Fig20. Typical switching energy losses as a function of IDS. 2nd device own body diode: VGS = 0/15 V, RG(ext) = 9.1 Ω, TVJ = 175 °C, VDS = 400 V

Fig21. Typical switching energy losses as a function of VDS. 2nd device own body diode: VGS = 0/15 V, RG(ext) = 9.1 Ω, TVJ = 175 °C, IDS = 4.5 A

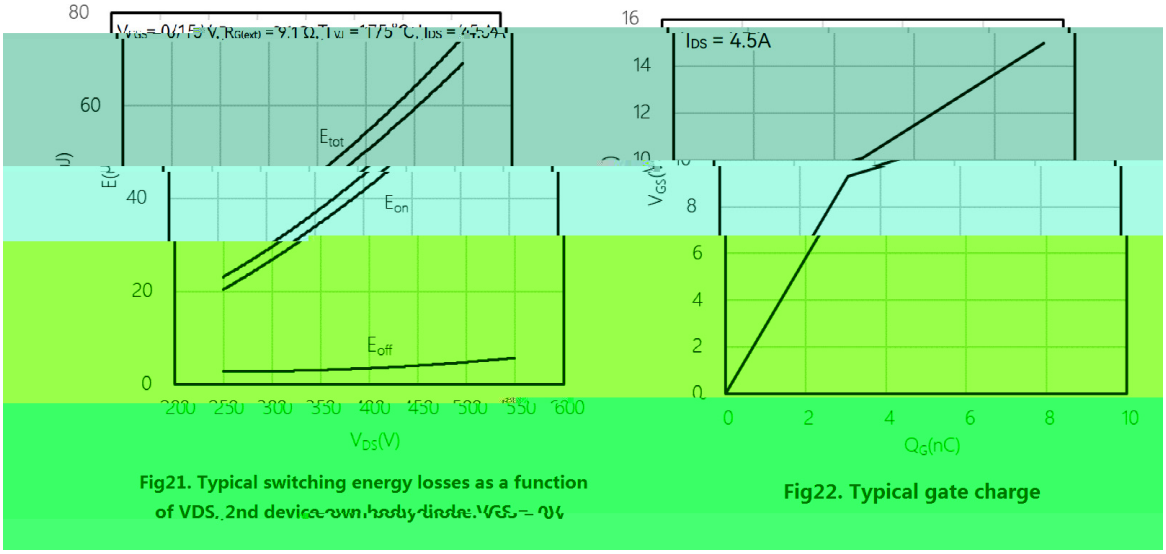


Fig22. Typical gate charge

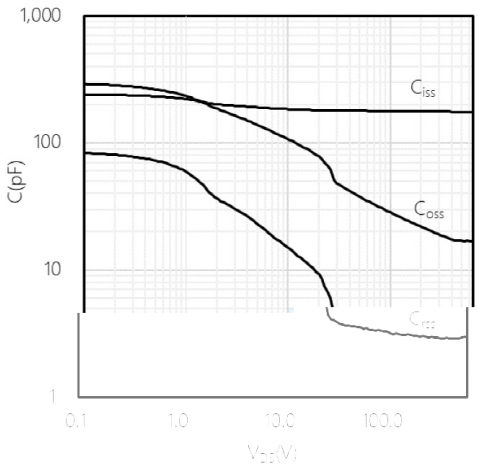


Fig23. Typical capacitance as a function of drain-source voltage

/ Electrical Characteristic Curve

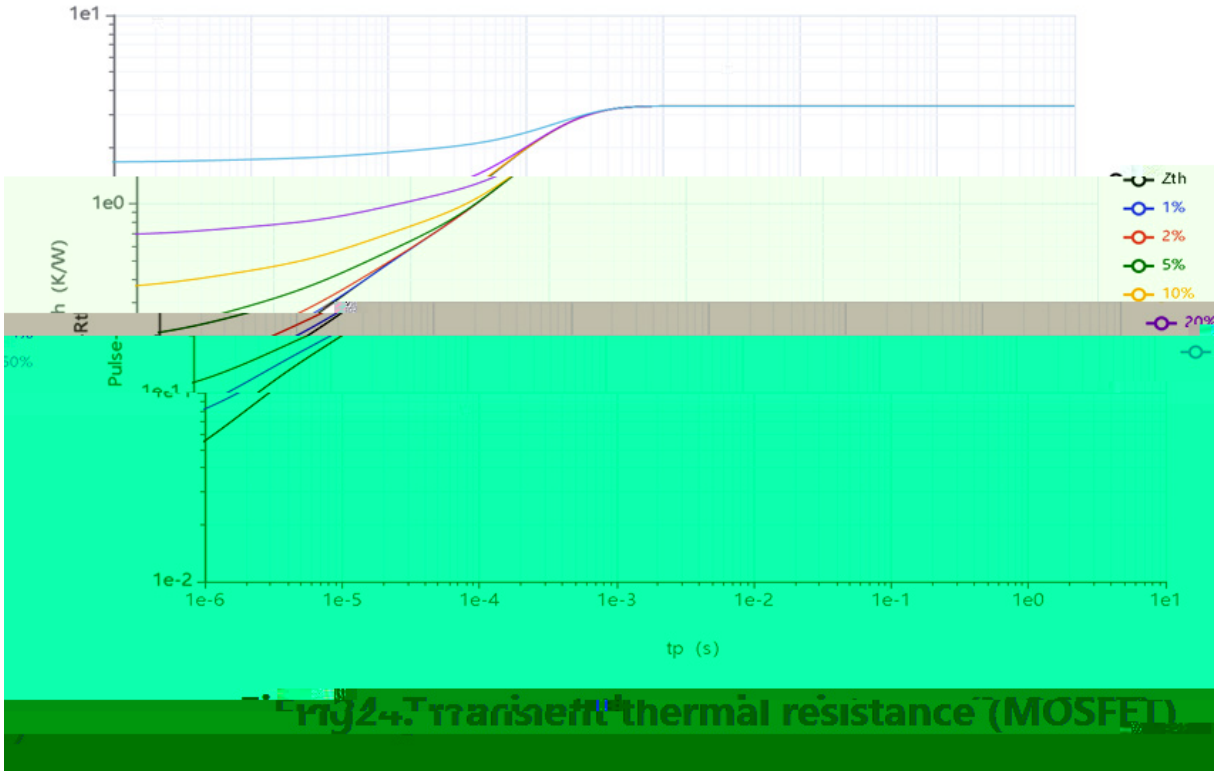
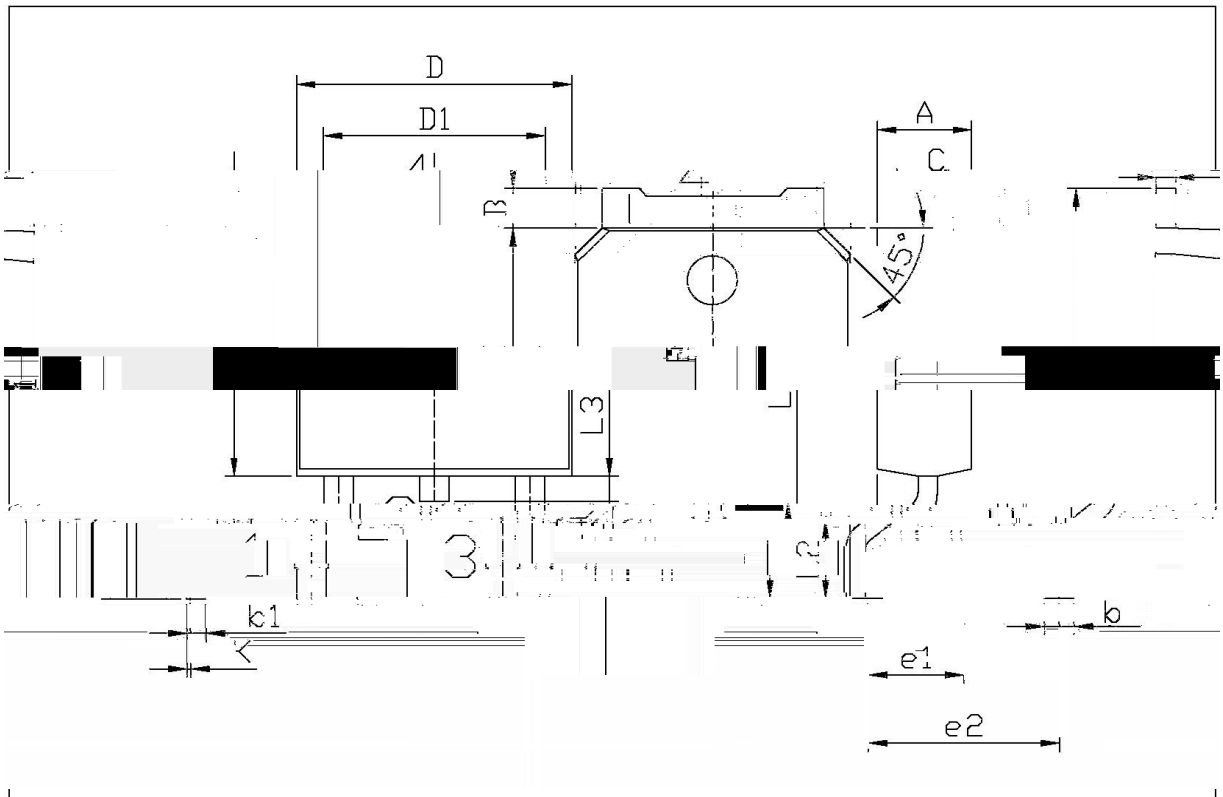


Fig24. Transient thermal resistance (MOSFET)

/ Package Dimensions



单位：mm

Symbol	Dimensions In Millimeters		Symbol	Dimensions In Millimeters	
	Min	Max		Min	Max
6.25	A	2.20	E	5.95	
2.34	B	0.95	e1	2.24	
4.73	b	0.70	e2	4.43	
10.35	b1	0.45	L1	9.85	
C	0.45	0.55	L2	1.70	2.00
L3	0.60	0.90	D	6.45	6.75
K	0.00	0.10	D1	5.10	5.50

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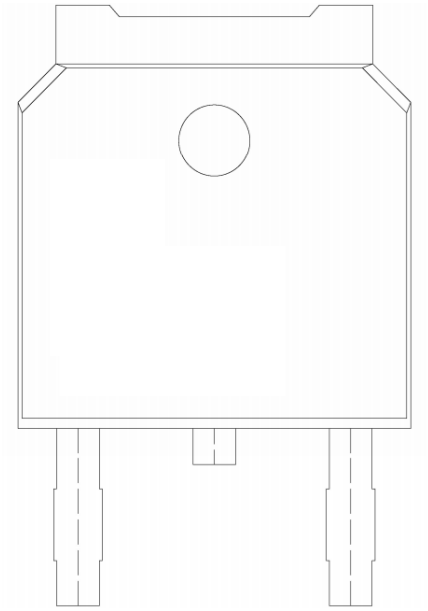
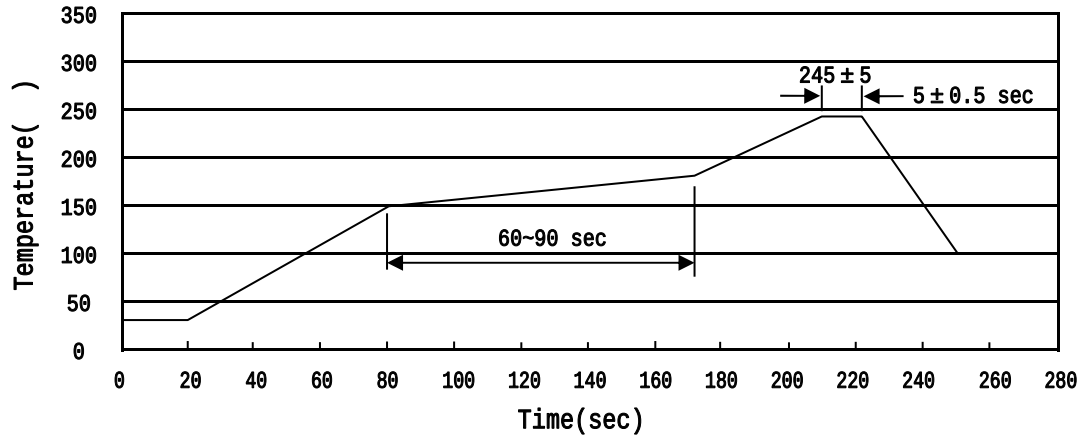
/ Marking Instructions



( ) / Temperature Profile for IR Reflow Soldering(Pb-Free)



/ Resistance to Soldering Heat Test Conditions

/ Packaging SPEC.

	Units/Reel /	Reels/Inner Box /	Units/Inner Box /	Inner Boxes/Outer Box /	Units/Outer Box /	Reel	Inner Box	Outer Box

	Units/Tube /	Tubes/Inner Box /	Units/Inner Box /	Inner Boxes/Outer Box /	Units/Outer Box /	Tube	Inner Box	Outer Box

/ Notices